S/N Unknown

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wendell P. Noble Jr.

Examiner:

Unknown Unknown

Serial No.:

Unknown

Group Art Unit:
Docket:

303.257US4

Filed: Title:

Herewith Docket: 303.237034

METHOD FOR FORMING GATE SEGMENTS FOR AN INTEGRATED

CIRCUIT

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicant's prior U.S. application, Serial No. <u>09/911688</u>, filed on <u>July 24, 2001</u>, which is relied upon for an earlier filing date under 35 U.S.C. §120.

Serial No :Unknown

Filing Date: Herewith

Title: METHOD FOR FORMING GATE SEGMENTS FOR AN INTEGRATED CIRCUIT

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The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

WENDELL P. NOBLE JR.

By his Representatives,

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Date 19 September 2003 By David R. Cochran

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This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to The Commissioner for Patents, Mail Stop Patent Application, P.O. Box 1450, Alexandria, VA 22313-1450.

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Complete if Known Substitute for form 1449A/PTO INFORMATION DISCLOSURE **Application Number** Unknown STATEMENT BY APPLICANT Even Date Herewith Filing Date (Use as many sheets as necessary) Noble Jr., Wendell **First Named Inventor Group Art Unit** Unknown Unknown **Examiner Name** Attorney Docket No: 303.257US4 Sheet 1 of 1

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DATE CONSIDERED EXAMINER